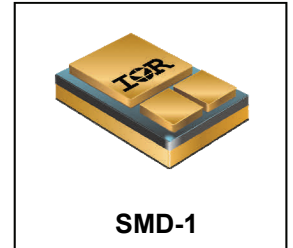


**RADIATION HARDENED
POWER MOSFET
SURFACE MOUNT (SMD-1)**

200V, N-CHANNEL
REF: MIL-PRF-19500/603
RAD-Hard HEXFET TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	I _D	QPL Part Number
IRHN7250	100 kRads(Si)	0.10Ω	26A	JANSR2N7269U
IRHN3250	300 kRads(Si)	0.155Ω	26A	JANSF2N7269U
IRHN4250	500 kRads(Si)	0.155Ω	26A	JANSG2N7269U
IRHN8250	1000 kRads(Si)	0.155Ω	26A	JANSH2N7269U



Description

IRHN7250 is part of the International Rectifier HiRel family of products. IR HiRel RAD-Hard HEXFET technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low R_{ds(on)} and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features

- Single Event Effect (SEE) Hardened
- Low RDS(on)
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Electrically Isolated
- Ceramic package
- Light Weight
- Surface Mount
- ESD Rating: Class 3A per MIL-STD-750, Method 1020

Absolute Maximum Ratings

	Parameter		Pre-Irradiation Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	26	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	16	
I _{DM}	Pulsed Drain Current ①	104	
P _D @ T _C = 25°C	Maximum Power Dissipation	150	W
	Linear Derating Factor	1.2	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy ②	500	mJ
I _{AR}	Avalanche Current ①	26	A
E _{AR}	Repetitive Avalanche Energy ①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (for 5sec)	
	Weight	2.6 (Typical)	

For Footnotes, refer to the page 2.

Electrical Characteristics @ T_J = 25°C (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.27	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.10	Ω	V _{GS} = 12V, I _D = 16A ④
		—	—	0.11		V _{GS} = 12V, I _D = 26A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
G _{fs}	Forward Transconductance	8.0	—	—	S	V _{DS} = 15V, I _D = 16A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	V _{DS} = 160V, V _{GS} = 0V
		—	—	250		V _{DS} = 160V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _G	Total Gate Charge	—	—	170	nC	I _D = 26A
Q _{GS}	Gate-to-Source Charge	—	—	30		V _{DS} = 100V
Q _{GD}	Gate-to-Drain ('Miller') Charge	—	—	60		V _{GS} = 12V
t _{d(on)}	Turn-On Delay Time	—	—	33	ns	V _{DD} = 100V
t _r	Rise Time	—	—	140		I _D = 26A
t _{d(off)}	Turn-Off Delay Time	—	—	140		R _G = 2.35Ω
t _f	Fall Time	—	—	140		V _{GS} = 12V
L _S + L _D	Total Inductance	—	6.8	—	nH	Measured from center of Drain pad to center of Source pad
C _{iss}	Input Capacitance	—	4700	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	850	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	210	—		f = 1.0MHz

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	26	A	
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	104		
V _{SD}	Diode Forward Voltage	—	—	1.4	V	T _J = 25°C, I _S = 26A, V _{GS} = 0V④
t _{rr}	Reverse Recovery Time	—	—	820	ns	T _J = 25°C, I _F = 26A, V _{DD} ≤ 30V
Q _{rr}	Reverse Recovery Charge	—	—	12	μC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	—	0.83	°C/W
R _{θPCB}	Junction-to-PC Board (soldered to 1 inch square cu clad board)	—	6.6	—	

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V_{DD} = 50V, starting T_J = 25°C, L = 1.5mH, Peak I_L = 26A, V_{GS} = 12V
- ③ I_{SD} ≤ 26A, di/dt ≤ 190A/μs, V_{DD} ≤ 200V, T_J ≤ 150°C
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%
- ⑤ **Total Dose Irradiation with V_{GS} Bias.** 12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.** 160 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100 kRads (Si) ¹		300k - 1000 kRads (Si) ²		Units	Test Conditions
		Min.	Max.	Min.	Max.		
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	200	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0	1.25	4.5	V	V _{DS} = V _{GS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100	nA	V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	25	—	50	μA	V _{DS} = 160V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.10	—	0.155	Ω	V _{GS} = 12V, I _D = 16A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (SMD-1)	—	0.10	—	0.155	Ω	V _{GS} = 12V, I _D = 16A
V _{SD}	Diode Forward Voltage	—	1.4	—	1.4	V	V _{GS} = 0V, I _D = 26A

1. Part number IRHN7250 (JANSR2N7269U)

2. Part numbers IRHN3250 (JANSF2N7269U), IRHN4250 (JANSR2N7269U) and IRHN8250 (JANSH2N7269U)

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	VDS (V)				
				@VGS=0V	@VGS=-5V	@VGS=-10V	@VGS=-15V	@VGS=-20V
Cu	28	285	43	190	180	170	125	—
Br	36.8	305	39	100	100	100	50	—

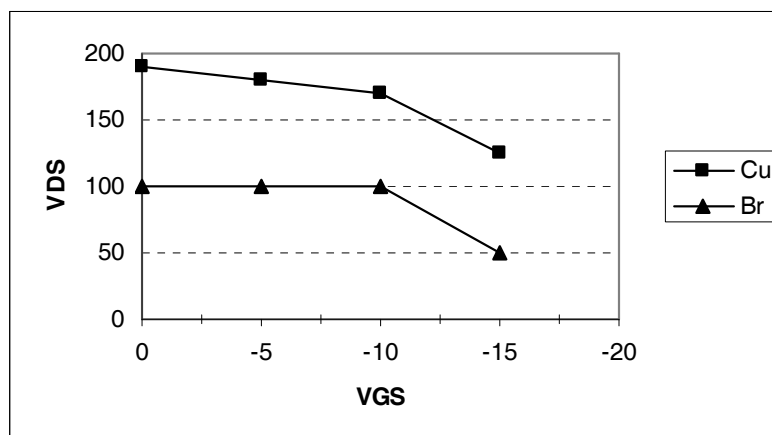


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

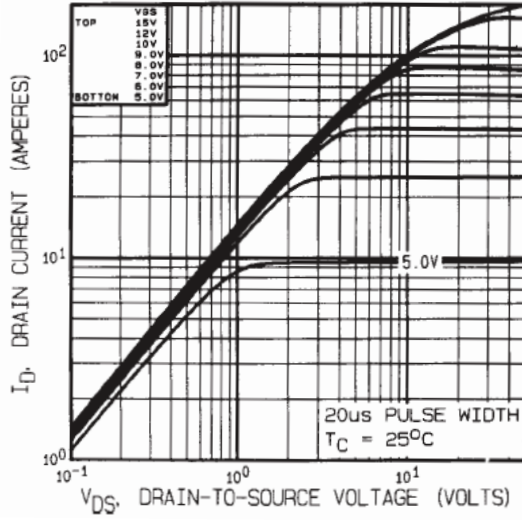


Fig 1. Typical Output Characteristics

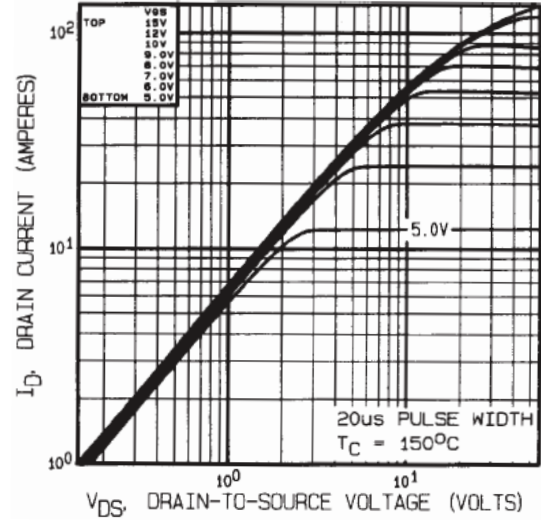


Fig 2. Typical Output Characteristics

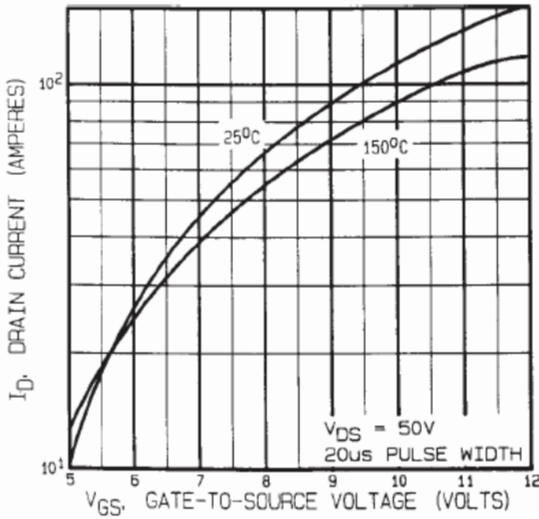


Fig 3. Typical Transfer Characteristics

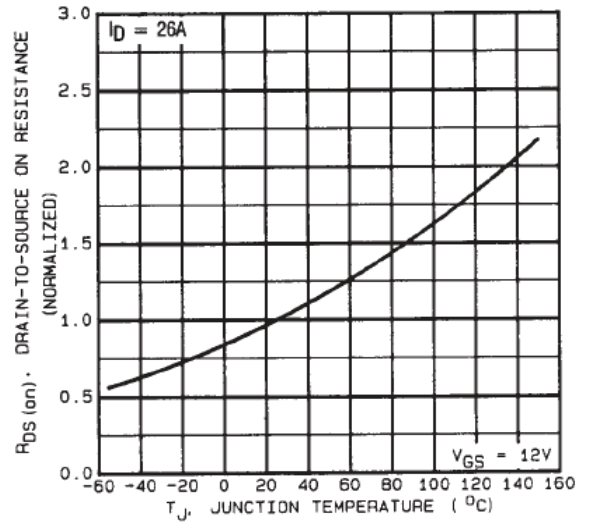


Fig 4. Normalized On-Resistance Vs. Temperature

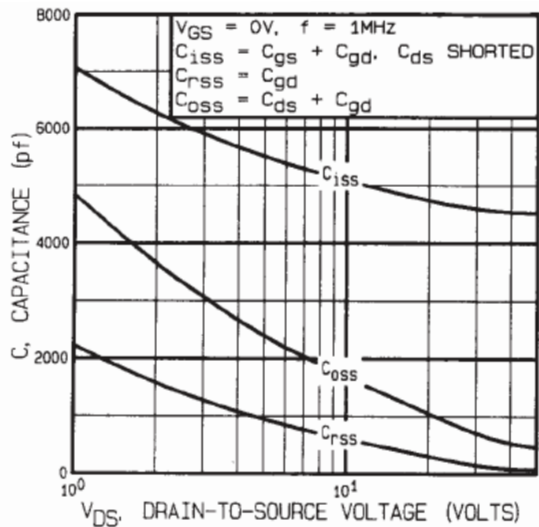


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

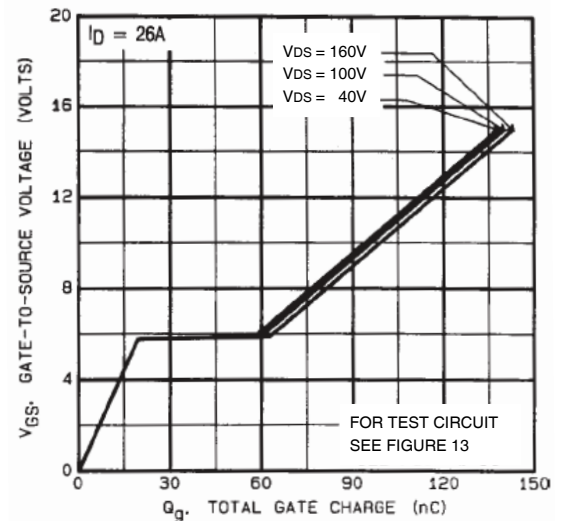


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

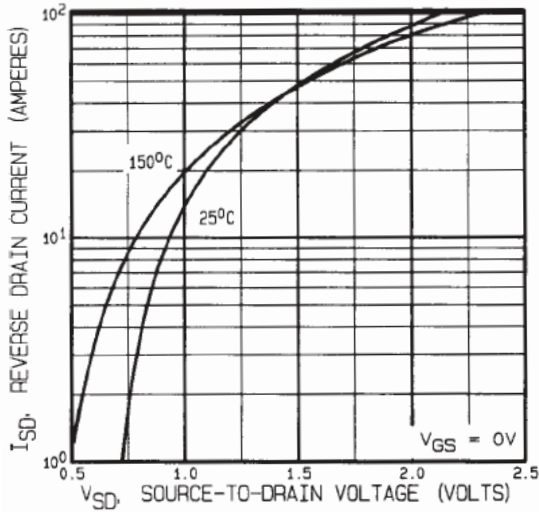


Fig 7. Typical Source-Drain Diode Forward Voltage

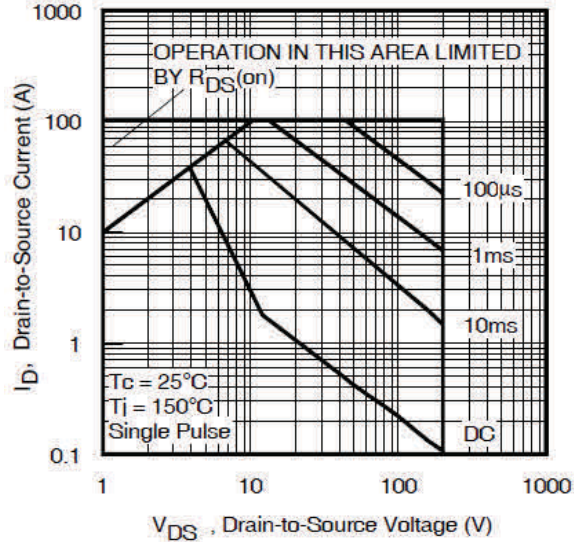


Fig 8. Maximum Safe Operating Area

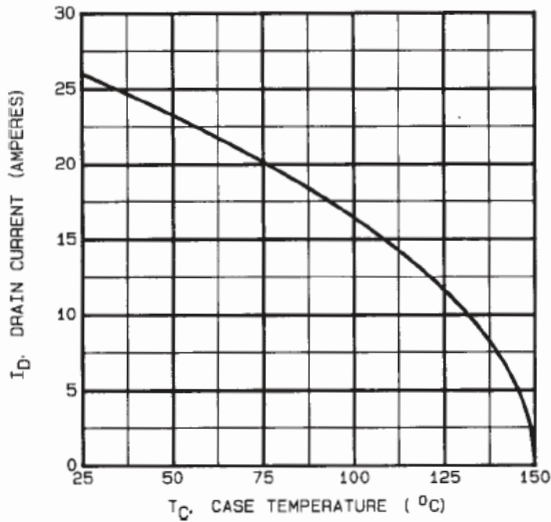


Fig 9. Maximum Drain Current Vs. Case Temperature

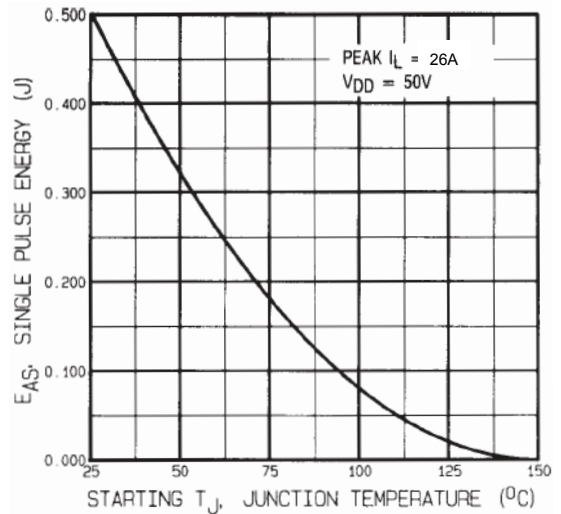


Fig 10. Maximum Avalanche Energy Vs. Drain Current

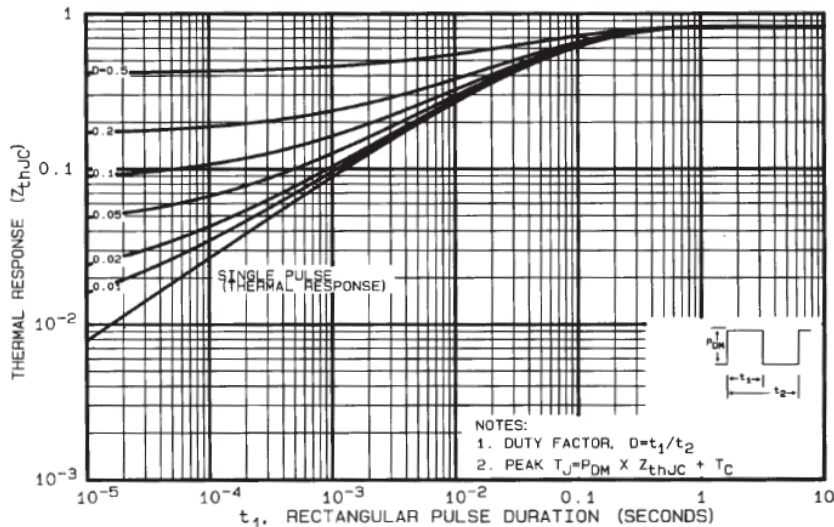


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

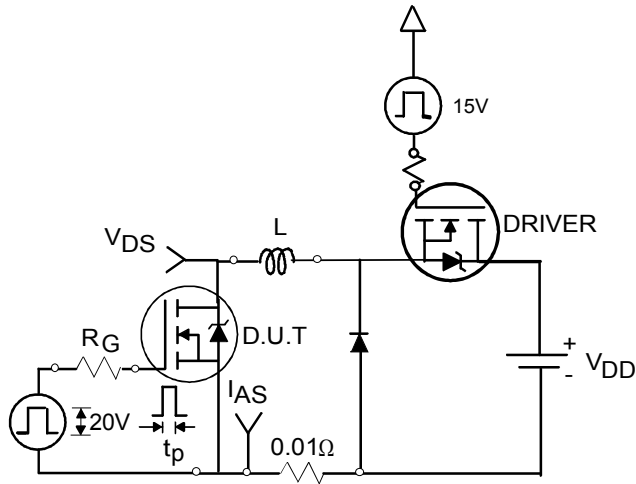


Fig 12a. Unclamped Inductive Test Circuit

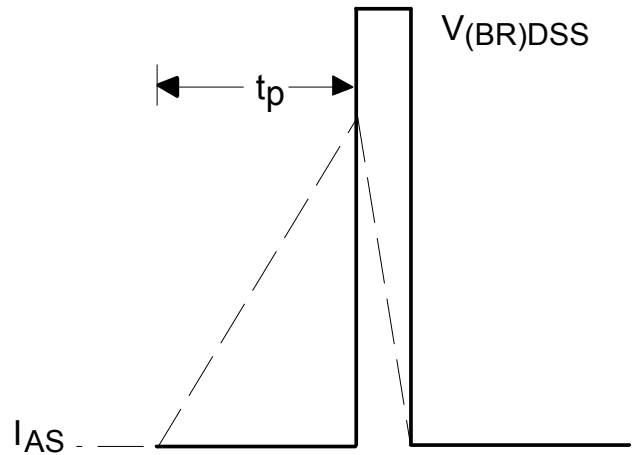


Fig 12b. Unclamped Inductive Waveforms

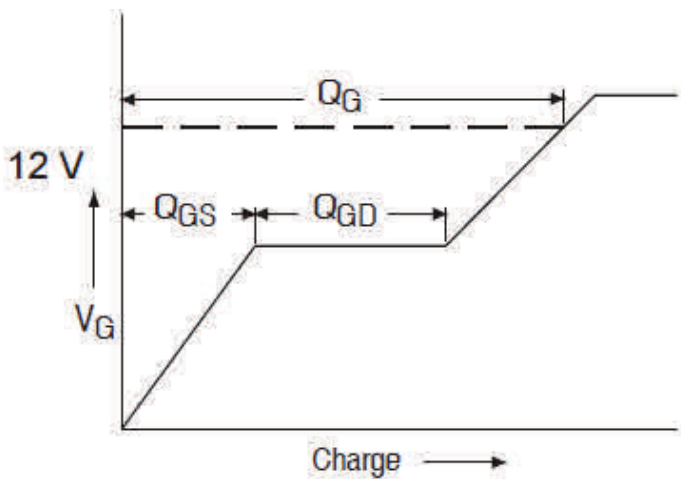


Fig 13a. Gate Charge Waveform

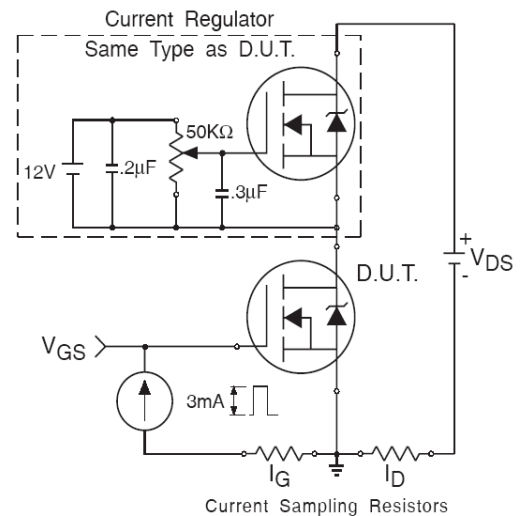


Fig 13b. Gate Charge Test Circuit

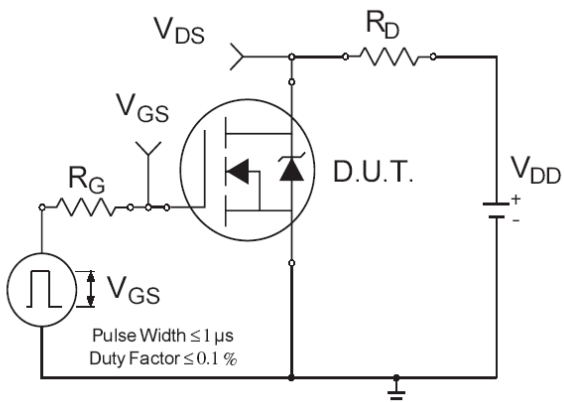


Fig 14a. Switching Time Test Circuit

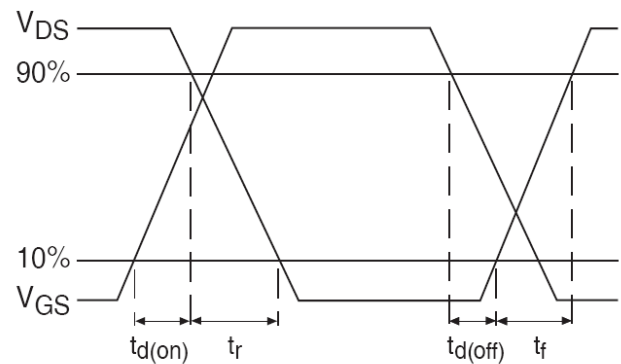
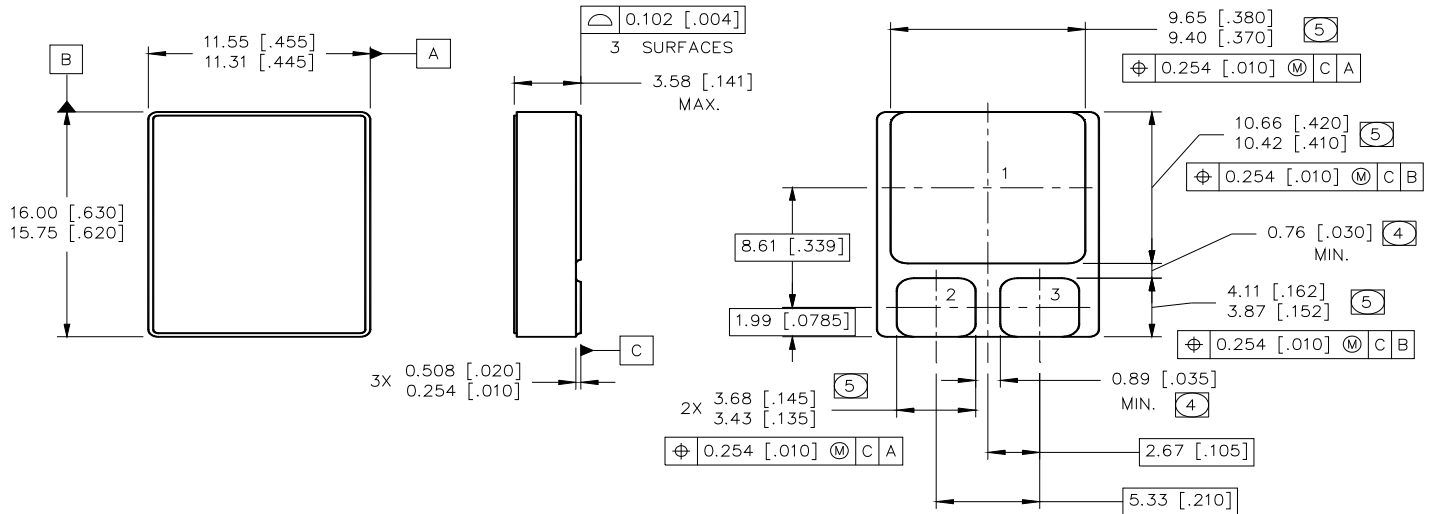


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions — SMD-1



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 4 DIMENSION INCLUDES METALLIZATION FLASH.
5 DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

<u>MOSFET</u>	
1	= DRAIN
2	= GATE
3	= SOURCE

IMPORTANT NOTICE

The information given in this document shall be in no event regarded as guarantee of conditions or characteristic. The data contained herein is a characterization of the component based on internal standards and is intended to demonstrate and provide guidance for typical part performance. It will require further evaluation, qualification and analysis to determine suitability in the application environment to confirm compliance to your system requirements.

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